

Product / Process Change Notice

Parts Affected:

Chip process CP707, NPN silicon small signal transistors, wafers, and bare die.

Extent of Change:

The CP707 wafer process has been discontinued and replaced with the CP727V wafer process.

The overall wafer diameter was increased from 4 inch to 5 inch.

The overall wafer thickness was reduced from 9 mils to 7.1 mils.

The backside metallization (Au) was reduced from 18,000Å to 9,000Å.

The die size was reduced from 27 x 27 mils to 22.8 x 22.8 mils.

The die pattern and bond pad area were changed; see figures 1 and 2 for details.

Reason for Change:

Process transfer from the 4" wafer fab to the 5" wafer fab.

Effect of Change:

This change does not affect the electrical characteristics of any device.

Qualification:

Standard evaluation and qualifications completed resulting in no performance differences compared to current product.

Effective Date of Change:

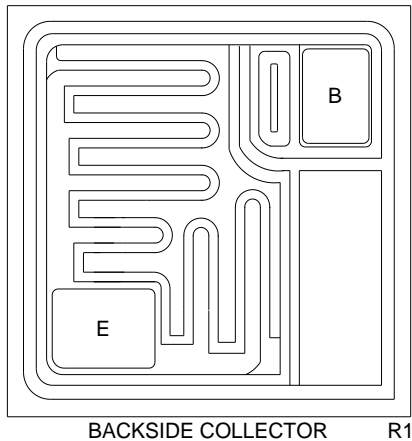
May 1, 2015. Existing inventory will be shipped until depleted.

Sample Availability:

Please contact Salesperson or Manufacturer's Representative.

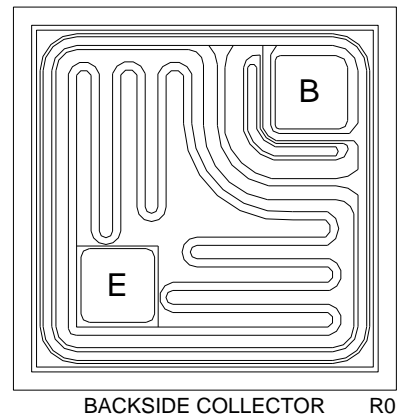
Figures:

Figure 1: CP707 Chip Geometry (Discontinued)



Wafer Diameter: 4 inch
Die Size: 27 x 27 mils
Die Thickness: 9.0 mils
Bond Pad Size (Emitter): 5.3 x 6.5 mils
Bond Pad Size (Base): 5.3 x 3.8 mils
Topside Metal: Al (30,000Å)
Backside Metal: Au (18,000Å)

Figure 2: CP727V Chip Geometry



Wafer Diameter: 5 inch
Die Size: 22.8 x 22.8 mils
Die Thickness: 7.1 mils
Bond Pad Size (Emitter): 4.7 x 4.7 mils
Bond Pad Size (Base): 4.7 x 4.7 mils
Topside Metal: Al (30,000Å)
Backside Metal: Au (9,000Å)

Part Numbers Affected:

- | | |
|---------|-------------------|
| MPSA62 | CMPTA77 |
| MPSA63 | CP707-MPSA64-WN |
| MPSA64 | CP707-MPSU95-WN |
| MPSA65 | CP707-CMPTA64-CTO |
| MPSA66 | CP707-MPSU95-CT |
| MPSA75 | |
| MPSA76 | |
| MPSA77 | |
| CXTA62 | |
| CXTA64 | |
| CZTA64 | |
| CZTA77 | |
| CEN-U95 | |
| CMPTA63 | |
| CMPTA64 | |